

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re U.S. Patent Application of)
SATO et al.)
Application Number: To be Assigned)
Filed: Concurrently Herewith)
For: MANUFACTURING METHOD OF SEMICONDUCTOR)
LASER DIODE)
ATTORNEY DOCKET NO. NITT.0191)

Honorable Assistant Commissioner
for Patents
Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT

Sir:

Pursuant to 37 C.F.R. §§ 1.56 and 1.97, this Information Disclosure Statement is submitted in the above-identified patent application. A listing of documents to be published on the face of any patent granted from this application is submitted herewith on Form PTO-1449. Any other documents or information submitted for consideration by the Examiner are listed in this paper. A copy of each U.S. and foreign patent, or each publication or portion thereof listed or herein identified, submitted herewith.

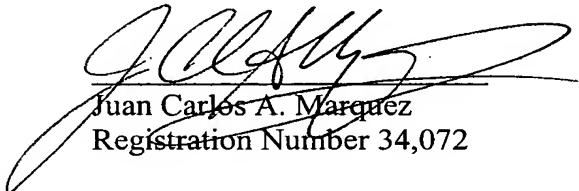
This Information Disclosure Statement is submitted with the initial filing of the application. Accordingly, no fee is due or payable at this time.

The Examiner is requested to acknowledge consideration of the information provided in this paper in accordance with prescribed procedures.

Please charge any additional fees or credit any overpayments in connection with this paper to Deposit Account No. 08-1480.

Respectfully submitted,

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Form PTO 1449 U.S. Department of Commerce Patent and Trademark Office Information Disclosure Statement by Applicant	ATTY. DOCKET NUMBER NITT.0191	SERIAL NUMBER To be Assigned
	APPLICANT Sato et al.	
	FILING DATE Concurrently Herewith	GROUP

U.S. Patent Documents

Examiner Initial	DOCUMENT NUMBER	DATE	NAME	CLA SS	SUBC LASS	FILING DATE

Foreign Patent Documents

Examiner Initial	DOCUMENT NUMBER	FILING DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION	
						YES	NO
	2003-78213	9/5/2001	Japan			Abstract	X
	2001-102355	7/26/2000	Japan			Abstract	X
	10-335756	6/5/97	Japan			Abstract	X

Other Documents (Including Author, Title, Date Pertinent Pages, Etc.)

		M. Aoki et al., "85°C-10Gbit/s Operation of 1.30µm InGaAlAs MQW-DFB Laser", 26 th European conference (ECOC2000), Vol 1, 2 pages
		P.J.A. Thijs et al., "High Performance Buried Heterostructure λ = 1.5 µm InGaAs/AlGaInAs Strained-Layer Quantum Well Laser Diodes", International Conference on Indium Phosphide and Related Materials, Conference Proceedings 1996, pp. 765-768
		K. Shinoda et al., "Highly Reliable InGaAsP/InP Lasers with Defect-Free Regrowth Interfaces formed by Newly Composed HBr-Based Solutions", 2001 IEEE, 2001 International Conference on Indium Phosphide and Related Materials, pp. 409-412
		D. Bertone et al., "High Reliability, High Yield, High Modulation Bandwidth, Low Threshold Current 1.55 µm MQW Laser by New In-Situ Etching Technique", 24 th European Conference on Optical Communication (ECOC 1998) Proceedings, Vol. 1, pp. 75-76
EXAMINER		DATE CONSIDERED
EXAMINER: Initial if citation is considered, whether or not citation is in conformance with MPEP 609; draw a line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant		